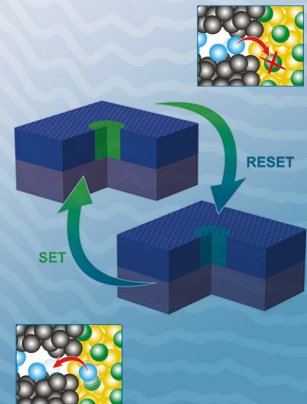
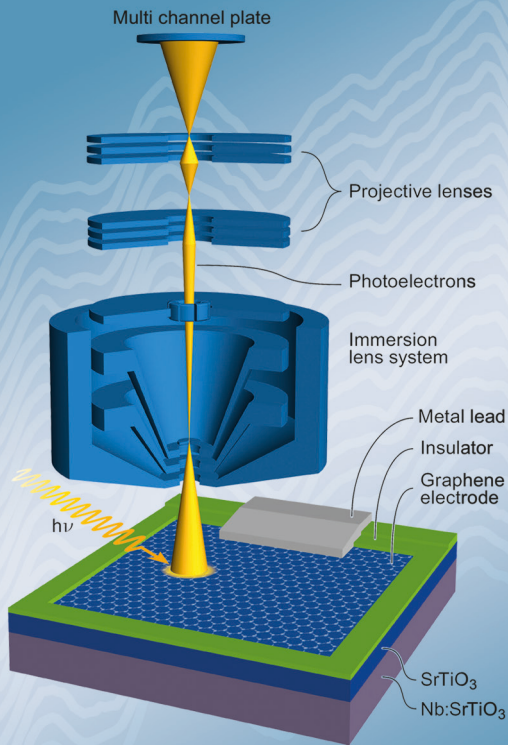


Spectroscopic characterization of local valence change processes in resistively switching complex oxides

Christoph Bäumler



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